Octal 3-State Noninverting Bus Transceiver

High-Performance Silicon-Gate CMOS

The MC74HC245A is identical in pinout to the LS245. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC245A is a 3-state noninverting transceiver that is used for 2-way asynchronous communication between data buses. The device has an active-low Output Enable pin, which is used to place the I/O ports into high-impedance states. The Direction control determines whether data flows from A to B or from B to A.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A

LOGIC DIAGRAM

• Chip Complexity: 308 FETs or 77 Equivalent Gates

16 B3 15 B4 14 B5 DATA DATA **PORT PORT** 13 B6 12 B7 11 B8 DIRECTION **OUTPUT ENABLE**

FUNCTION TABLE

PIN 10 = GND $PIN 20 = V_{CC}$

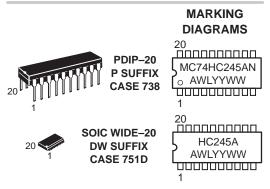
Contro	l Inputs		
Output Enable	Direction	Operation	
L	L	Data Transmitted from Bus B to Bus A	
L	Н	Data Transmitted from Bus A to Bus B	
Н	Х	Buses Isolated (High-Impedance State)	

X = don't care



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= Assembly Location

WL = Wafer Lot YY = Year

WW = Work Week

PIN ASSIGNMENT

			-
DIRECTION [1•	20	v _{CC}
A1 [2	19	OUTPUT ENABLE
A2 [3	18	D B1
A3 [4	17	D B2
A4 [5	16	D B3
A5 [6	15	D B4
A6 [7	14	р в5
A7 [8	13	D B6
A8 [9	12	D B7
GND [10	11	D B8
			•

ORDERING INFORMATION

Device	Package	Shipping			
MC74HC245AN	PDIP-20	1440 / Box			
MC74HC245ADW	SOIC-WIDE	38 / Rail			
MC74HC245ADWR2	SOIC-WIDE	1000 / Reel			

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{I/O}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
l _{in}	DC Input Current, per Pin	± 20	mA
I _{I/O}	DC Output Current, per Pin	± 35	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 75	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Functional operation should be restricted to the Recommended Operating Conditions.

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
VCC	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			VCC	V
TA	Operating Temperature, All Package Types			+ 125	°C
t _r , t _f	Input Rise and Fall Time VCC (Figure 1) VCC VCC	= 2.0 V = 4.5 V = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{\text{Out}} = V_{\text{CC}} - 0.1 \text{ V}$ $ I_{\text{Out}} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
VIL	Maximum Low–Level Input Voltage	$V_{\text{Out}} = 0.1 \text{ V}$ $ I_{\text{Out}} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
VOH	Minimum High–Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	٧
		$\begin{aligned} V_{in} = V_{IH} & I_{out} \leq 2.4 \text{ m.} \\ I_{out} \leq 6.0 \text{ m.} \\ I_{out} \leq 7.8 \text{ m.} \end{aligned}$	4.5	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
VOL	Maximum Low–Level Output Voltage	$ V_{\text{in}} = V_{\text{IL}} $ $ I_{\text{Out}} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	٧
		$\begin{aligned} V_{in} = V_{IL} & I_{out} \leq 2.4 \text{ m.} \\ I_{out} \leq 6.0 \text{ m.} \\ I_{out} \leq 7.8 \text{ m.} \end{aligned}$	4.5	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

[†]Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	v _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
loz	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	6.0	± 0.5	± 5.0	± 10	μА
ICC	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 µA	6.0	4.0	40	160	μА

NOTE: Information on typical parametric values and high frequency or heavy load considerations can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

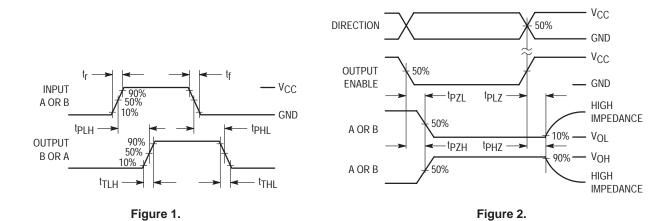
			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to B, B to A (Figures 1 and 3)	2.0 3.0 4.5 6.0	75 55 15 13	95 70 19 16	110 80 22 19	ns
tPLZ, tPHZ	Maximum Propagation Delay, Direction or Output Enable to A or B (Figures 2 and 4)		110 90 22 19	140 110 28 24	165 130 33 28	ns
tPZL [,] tPZH	Maximum Propagation Delay, Output Enable to A or B (Figures 2 and 4)		110 90 22 19	140 110 28 24	165 130 33 28	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 23 12 10	75 27 15 13	90 32 18 15	ns
C _{in}	Maximum Input Capacitance (Pin 1 or Pin 19)	_	10	10	10	pF
C _{out}	Maximum Three–State I/O Capacitance (I/O in High–Impedance State)	_	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

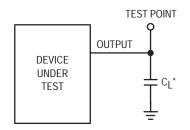
		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Transceiver Channel)*	40	pF

^{*} Used to determine the no-load dynamic power consumption: PD = CPD VCC²f + ICC VCC. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS

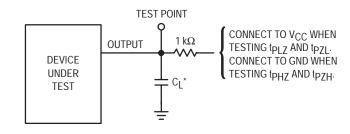


TEST CIRCUITS



*Includes all probe and jig capacitance

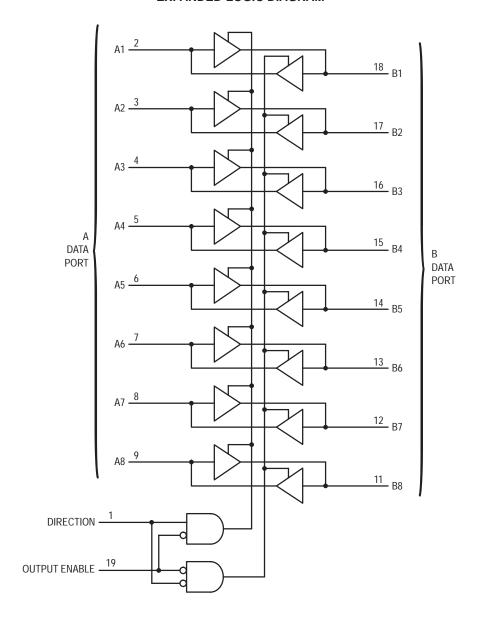
Figure 3.



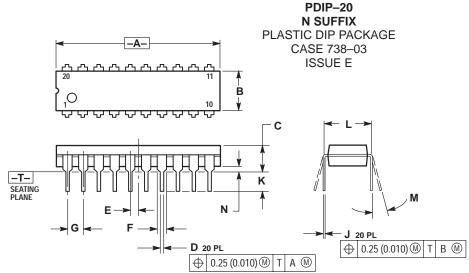
*Includes all probe and jig capacitance

Figure 4.

EXPANDED LOGIC DIAGRAM



PACKAGE DIMENSIONS



NOTES:

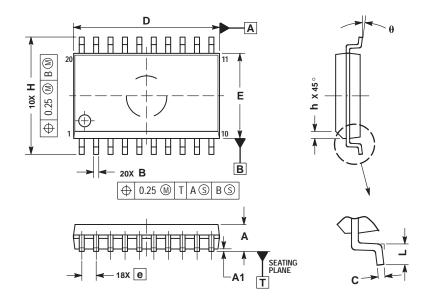
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 1 14.3W, 1702.

 CONTROLLING DIMENSION: INCH.

 DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
С	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
Ε	0.050 BSC		1.27 BSC		
F	0.050	0.070	1.27	1.77	
G	0.100	BSC	2.54 BSC		
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
L	0.300 BSC 7.62 B		BSC		
M	0 °	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

SO-20 **DW SUFFIX** CASE 751D-05 ISSUE F



- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

- PER ASME 174-5M, 1994.

 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
Ε	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

Notes

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